VMB40-12S

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI VMB40-12S** is Designed for 12.5 V, Medium Band Class C Application.

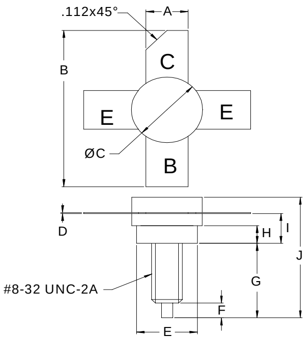
FEATURES:

- Common Emitter
- **P_G** = 10 dB at 40 W/175 MHz
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	5.0 A
V_{CBO}	36 V
V_{CEO}	18 V
V_{EBO}	4.0 V
P_{DISS}	70 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.5 °C/W

PACKAGE STYLE .380 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

ORDER CODE: ASI10744

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 50 mA	18			V
BV_{CES}	I_C = 50 mA	36			V
BV_{CBO}	I_C = 50 mA	36			
BV_{EBO}	I_E = 10 mA	4.0			V
I_{CES}	V_{CE} = 12.5 V			5.0	mA
h_{FE}	V_{CE} = 5.0 V I_C = 5.0 A	20		200	---
C_{OB}	V_{CB} = 12.5 V f = 1.0 MHz			165	pF
P_G η_C	V_{CE} = 12.5 V P_{OUT} = 40 W f = 175 MHz	10	 60		dB %